C106B C106D C106M 4.0A SENSITIVE GATE SILICON CONTROLLED RECTIFIER 200 THRU 600 VOLTS



Central[™] Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR C106B Series are 4.0A, PNPN sensitive gate triggering silicon controlled rectifiers with voltages ranging from 200V to 600V. These devices are designed for applications such as temperature, light and speed control, remote warning and triggering applications.

MARKING CODE: FULL PART NUMBER

 $\textbf{MAXIMUM RATINGS:} \quad (T_{\hbox{C}} = 25^{\circ} \hbox{C unless otherwise noted)}$

| | SYMBOL | C106B | C106D | C106M | <u>UNITS</u> |
|---|---------------------|-------|------------|-------|--------------|
| Peak Repetitive Off-State Voltage | $V_{DRM, V_{RRM}}$ | 200 | 400 | 600 | V |
| RMS On-State Current (T _C =80°C) | I _{T(RMS)} | | 4.0 | | Α |
| Peak Non-Repetitive Surge Current (T _J =110°C) | ITSM | | 20 | | Α |
| I ² t Value for Fusing (t=8.3ms) | I ² t | | 1.65 | | A^2s |
| Peak Gate Power (T _C =80°C) | P_GM | | 0.5 | | W |
| Average Gate Power (T _C =80°C) | $P_{G(AV)}$ | | 0.1 | | W |
| Peak Forward Gate Current (T _C =80°C) | I _{GFM} | | 0.2 | | Α |
| Storage Temperature | T_{stg} | | -40 to +15 | 50 | °C |
| Junction Temperature | TJ | | -40 to +11 | 0 | °C |
| Thermal Resistance | Θ JC | | 3.0 | | °C/W |
| Thermal Resistance | $\Theta_{\sf JA}$ | | 75 | | °C/W |

ELECTRICAL CHARACTERISTICS: (T_J=25°C unless otherwise noted)

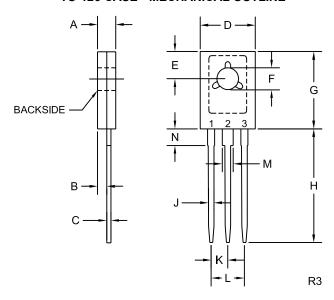
| SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|------------------------------------|--|-----|-----|-----|-------|
| I _{DRM,} I _{RRM} | Rated V_{DRM} , V_{RRM} , R_{GK} =1 $K\Omega$ | | | 10 | μΑ |
| I _{DRM,} I _{RRM} | Rated V_{DRM} , V_{RRM} , R_{GK} =1 $K\Omega$, T_{J} =110°C | | | 100 | μΑ |
| V_{TM} | I _{FM} =4.0A | | | 2.2 | V |
| l _{GT} | V_{AK} =6.0V, R_L =100 Ω | | | 200 | μΑ |
| l _{GT} | V_{AK} =6.0V, R_L =100 Ω , T_J = -40°C | | | 500 | μΑ |
| V_{GT} | V_{AK} =6.0V, R_L =100 Ω | 0.4 | | 8.0 | V |
| V_{GT} | V_{AK} =6.0V, R_L =100 Ω , T_J = -40°C | 0.5 | | 1.0 | V |
| lΗ | V _D =12V | | | 3.0 | mA |
| lΗ | V_D =12V, T_J = -40°C | | | 6.0 | mA |
| lΗ | V _D =12V, T _J =110°C | | | 2.0 | mA |
| IL | V _D =12V | | | 5.0 | mA |
| IL | V _D =12V, T _J = -40°C | | | 7.0 | mA |
| dv/dt | V_D = Rated V_{DRM} , R_{GK} =1 $K\Omega$, T_J =110°C | | 8.0 | | V/µs |

R0 (27-April 2004)



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TO-126 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) CATHODE
- 2) ANODE
- 3) GATE

MARKING CODE: FULL PART NUMBER

| DIMENSIONS | | | | | |
|-----------------|--------|-------|-------------|-------|--|
| | INCHES | | MILLIMETERS | | |
| SYMBOL | MIN | MAX | MIN | MAX | |
| Α | 0.094 | 0.110 | 2.40 | 2.80 | |
| В | 0.050 | | 1.27 | | |
| С | 0.015 | 0.030 | 0.38 | 0.75 | |
| D | 0.291 | 0.335 | 7.40 | 8.50 | |
| E | 0.148 | | 3.75 | | |
| F | 0.118 | 0.134 | 3.00 | 3.40 | |
| G | 0.413 | 0.472 | 10.50 | 12.00 | |
| Н | 0.618 | | 15.70 | | |
| J | 0.024 | 0.035 | 0.62 | 0.90 | |
| K | 0.089 | | 2.25 | | |
| L | 0.177 | | 4.50 | | |
| М | 0.045 | 0.055 | 1.14 | 1.40 | |
| N | 0.083 | | 2.10 | | |
| TO 400 (DEV/D0) | | | | | |

TO-126 (REV:R3)

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.